TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W139F, TC7W139FU

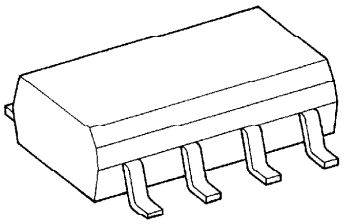
2-TO-4 LINE DECODER

The TC7W139 is a high speed C^2MOS 2 to 4 LINE DECODER / DEMULTIPLEXER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the C^2MOS low power dissipation.

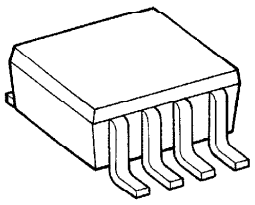
All inputs are equipped with protection circuits against static discharge or trasient excess voltage.

TC7W139F



SOP8-P-1.27

TC7W139FU



SSOP8-P-0.65

Weight SOP8-P-1.27 : 0.05g (Typ.)
SSOP8-P-0.65 : 0.02g (Typ.)

FEATURES

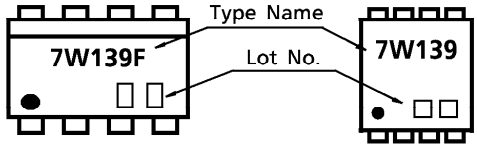
- High Speed ..... t_{pd} = 6ns (Typ.) at V_{CC} = 5V
- Low Power Dissipation ..... I_{CC} = 2μA (Max.) at Ta = 25°C
- High Noise Immunity ..... $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)
- Output Drive Capability ..... 10 LSTTL Loads
- Symmetrical Output Impedance ... $|I_{OH}| = I_{OL}$ = 4mA
- Balanced Propagation Delays ..... $t_{pLH} \fallingdotseq t_{pHL}$
- Wide Operating Voltage Range ... $V_{CC\,(opr)}$ = 2V~6V

TRUTH TABLE

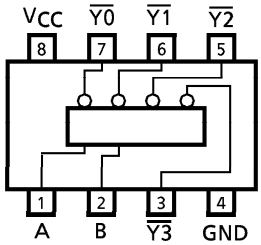
INPUTS		OUTPUTS				SELECTED OUTPUT
SELECT		$\overline{Y0}$	$\overline{Y1}$	$\overline{Y2}$	$\overline{Y3}$	
B	A					
L	L	L	H	H	H	$\overline{Y0}$
L	H	H	L	H	H	$\overline{Y1}$
H	L	H	H	L	H	$\overline{Y2}$
H	H	H	H	H	L	$\overline{Y3}$

MARKING

TC7W139F TC7W139FU



PIN ASSIGNMENT (TOP VIEW)



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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	−0.5~7	V
DC Input Voltage	V_{IN}	−0.5~V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	−0.5~V_{CC} + 0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±25	mA
DC V_{CC} / Ground Current	I_{CC}	±25	mA
Power Dissipation	P_D	300	mW
Storage Temperature	T_{stg}	−65~150	°C
Lead Temperature 10s	T_L	260	°C

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~V_{CC}	V
Output Voltage	V_{OUT}	0~V_{CC}	V
Operating Temperature	T_{opr}	−40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 (V_{CC} = 2.0V) 0~ 500 (V_{CC} = 4.5V) 0~ 400 (V_{CC} = 6.0V)	ns

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DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		V_{CC}	Ta = 25°C MIN.	Ta = 25°C TYP.	Ta = 25°C MAX.	Ta = −40~85°C MIN.	Ta = −40~85°C MAX.	UNIT
High-Level Input Voltage	V_{IH}	—		2.0	1.5	—	—	1.5	—	V
				4.5	3.15	—	—	3.15	—	
				6.0	4.2	—	—	4.2	—	
Low-Level Input Voltage	V_{IL}	—		2.0	—	—	0.5	—	0.5	V
				4.5	—	—	1.35	—	1.35	
				6.0	—	—	1.8	—	1.8	
High-Level Output Voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −20μA	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0	—	5.9	—	
			I_{OH} = −4mA	4.5	4.18	4.31	—	4.13	—	
			I_{OH} = −5.2mA	6.0	5.68	5.80	—	5.63	—	
Low-Level Output Voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20μA	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
			I_{OL} = 4mA	4.5	—	0.17	0.26	—	0.33	
			I_{OL} = 5.2mA	6.0	—	0.18	0.26	—	0.33	
Input Leakage Current	I_{IN}	V_{IN} = V_{CC} or GND		6.0	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current	I_{CC}	V_{IN} = V_{CC} or GND		6.0	—	—	2.0	—	20.0	

AC ELECTRICAL CHARACTERISTICS (C_L = 15pF, V_{CC} = 5V, Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}	—	—	4	8	ns
Propagation Delay Time (A, B-$\overline{Y}$)	t_{pLH} t_{pHL}	—	—	12	22	

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input $t_r = t_f$ = 6ns)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = −40~85°C		UNIT
			V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time (A, B-$\overline{Y}$)	t_{pLH} t_{pHL}	—	2.0	—	45	130	—	165	
			4.5	—	15	26	—	33	
			6.0	—	13	22	—	28	
Input Capacitance	C_{IN}	—		—	5	10	—	10	pF
Power Dissipation Capacitance	C_{PD}	(Note 1)		—	46	—	—	—	

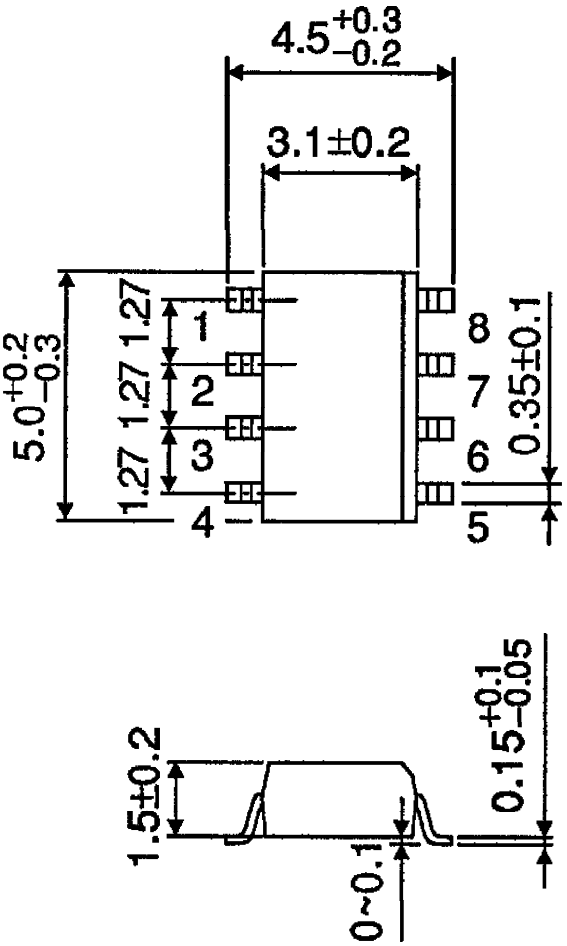
Note 1 : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation.

$$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

OUTLINE DRAWING

SOP8-P-1.27

Unit : mm

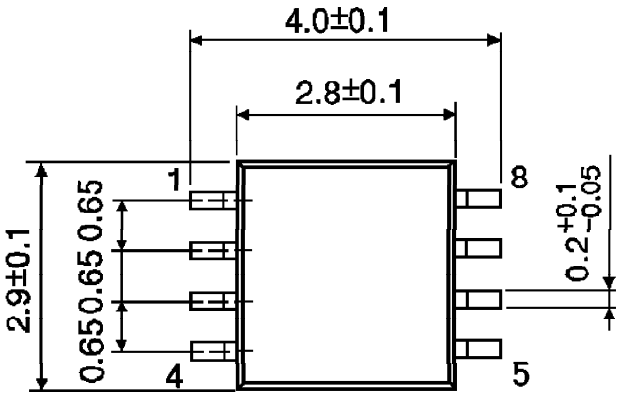


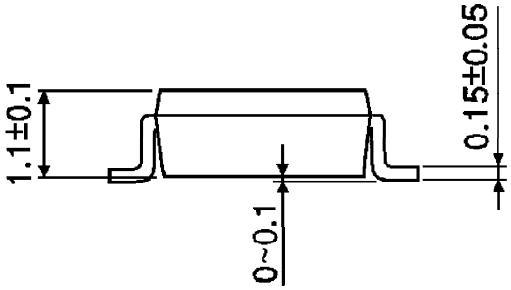
Weight : 0.05g (Typ.)

OUTLINE DRAWING

SSOP8-P-0.65

Unit : mm





Weight : 0.02g (Typ.)